

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1027	(dies wafer) with (substrate carrier board) with waveguide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:20
L3	240	2 and (dicing singulating singuated singulate cuting cutting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 14:22
L4	7	("5266528" "6055976" "6291317" "6346034" "6428883" "6429506" "6560848").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/05 15:11
L5	1954	dies with (mems (micro near1 electronic near1 mechanical near1 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 15:23
L6	5565	die with (mems (micro near1 electronic near1 mechanical near1 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 15:23
L7	2533	die near4 (mems (micro near1 electronic near1 mechanical near1 sensor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 15:23
L8	0	7 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 15:23
L9	310	7 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 15:23

EAST Search History

L10	32077	((insulating insulation dielectric) near1 (layer film material)) with (circuitry chip die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:02
L11	1776	10 and (((insulating insulation dielectric) near1 (layer film material)) with (cured cure curing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:03
L12	40	11 and (((insulating insulation dielectric) near1 (layer film material)) with grinding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:03
L13	21	12 and (metal near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:04
L14	163193	(dies wafer) with (substrate carrier board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:21
L15	4865	14 and ((dicing: cuting: cutting singulating singulated) near3 (substrate carrier board))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:22
L16	36	15 and ((passive near1 (device component element)) with (dies wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:27
L17	98	15 and (waveguide with (dies wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 16:45